

0908746 = 301300

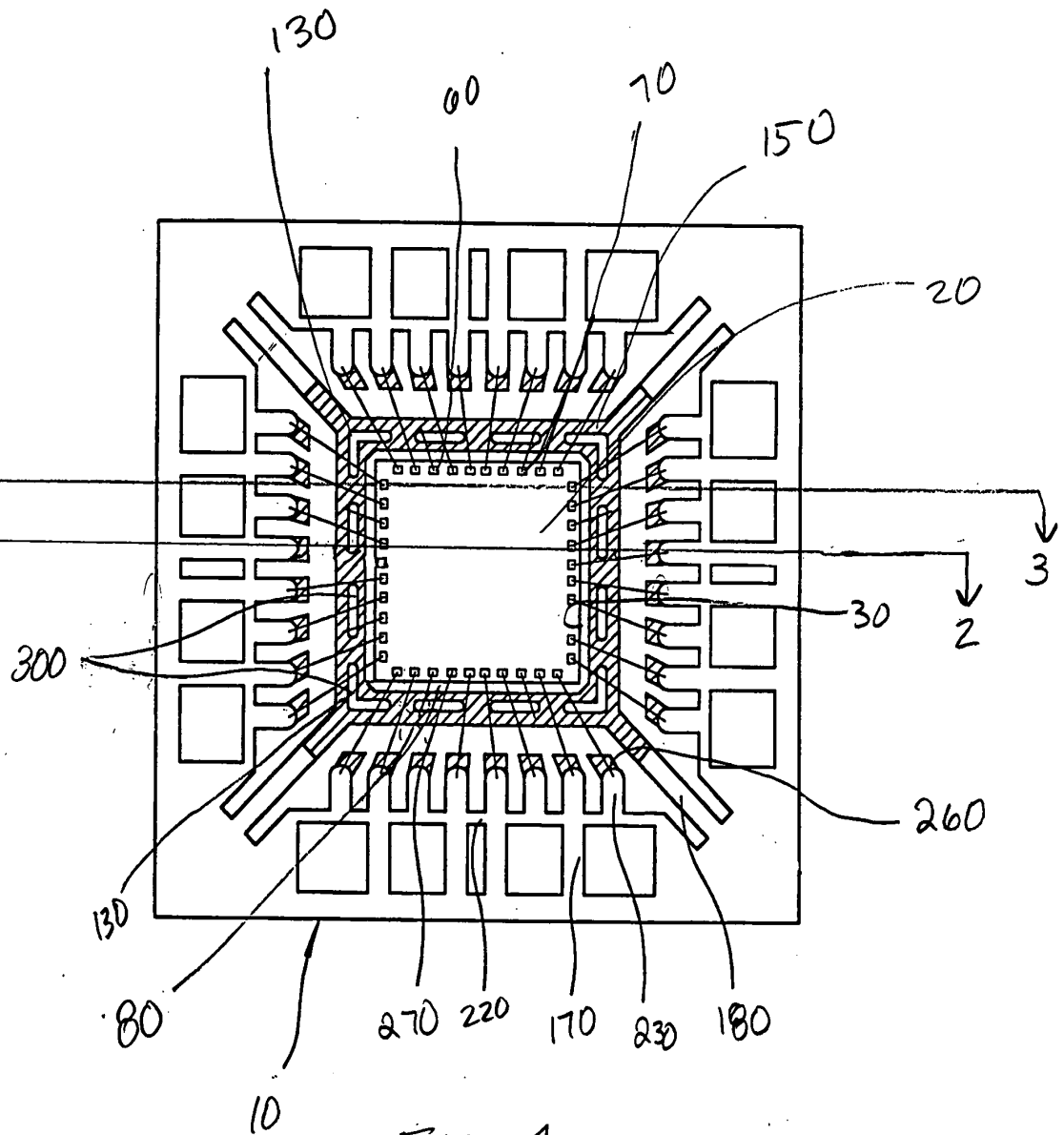
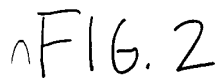


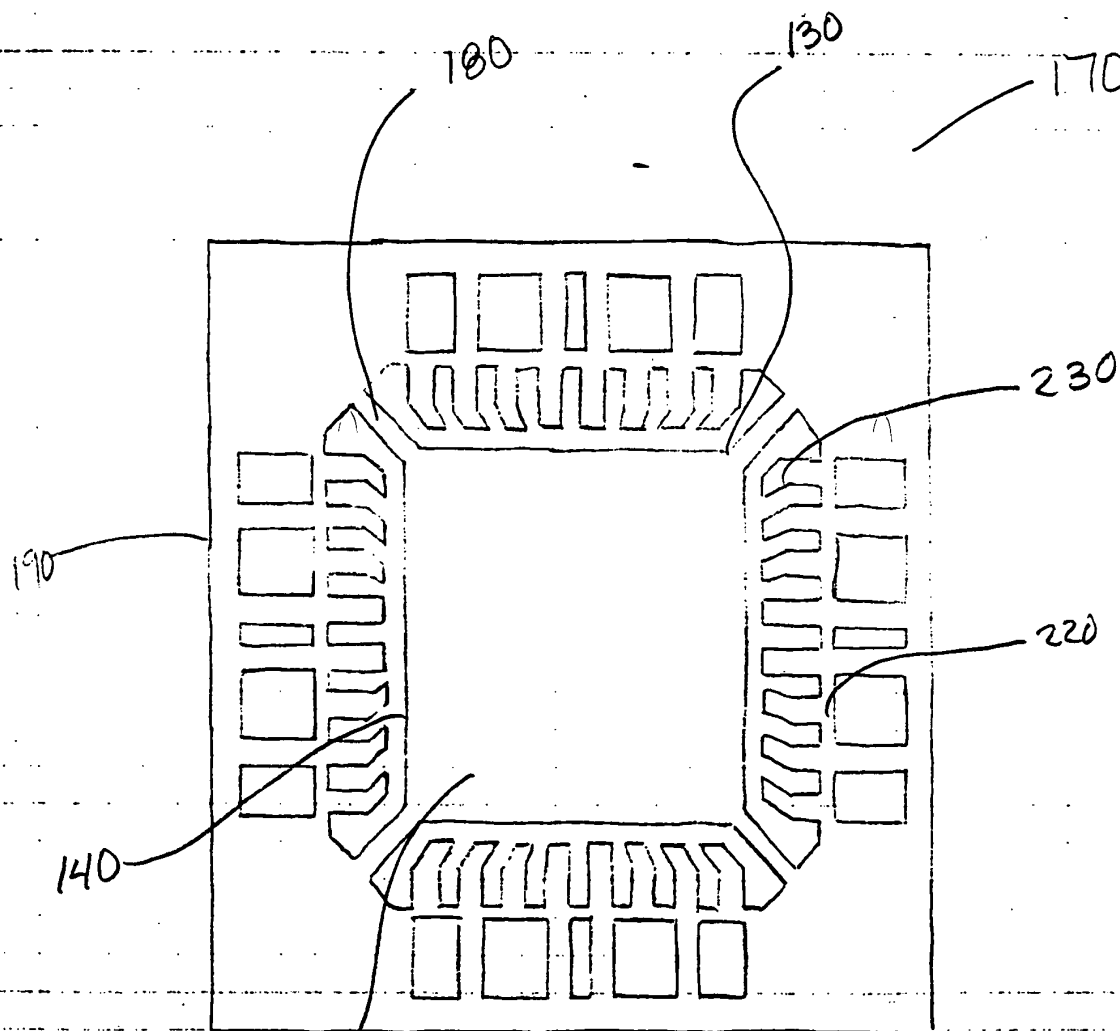
FIG. 1

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[illegible]

FIG. 3

Parameter	Unit	Value
Temperature	°C	25.0
Pressure	atm	1.0
Flow rate	L/min	1.0
Sample concentration	mg/mL	1.0
Sample volume	μL	1.0
Injection volume	μL	1.0
Column	mm	150 × 4.6
Mobile phase		Water
Detection		UV-Vis
Wavelength	nm	254
Scan rate	nm/min	10
Resolution	nm	0.5
Integration		Area
Baseline		Flat
Peak width	nm	0.5
Peak height	nm	0.5
Peak area	nm	0.5
Peak position	nm	0.5
Peak shape		Flat
Peak symmetry		Flat
Peak resolution		Flat
Peak quality		Flat
Peak purity		Flat
Peak identification		Flat
Peak classification		Flat
Peak annotation		Flat
Peak description		Flat
Peak comment		Flat
Peak note		Flat
Peak tag		Flat
Peak label		Flat
Peak title		Flat
Peak subtitle		Flat
Peak author		Flat
Peak coauthor		Flat
Peak reviewer		Flat
Peak editor		Flat
Peak publisher		Flat
Peak distributor		Flat
Peak retailer		Flat
Peak wholesaler		Flat
Peak manufacturer		Flat
Peak supplier		Flat
Peak importer		Flat
Peak exporter		Flat
Peak agent		Flat
Peak broker		Flat
Peak dealer		Flat
Peak distributor		Flat
Peak wholesaler		Flat
Peak manufacturer		Flat
Peak supplier		Flat
Peak importer		Flat
Peak exporter		Flat
Peak agent		Flat
Peak broker		Flat
Peak dealer		Flat



80

FIG. 4

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6

FIG. 5

A cross-sectional view of a semiconductor device 10. The device features a substrate 110 with a central layer 80. A top layer 20 is patterned into a central rectangular region 30 and side regions 260. The side regions 260 are filled with a material 270. A layer 60 is located between the top layer 20 and the substrate 110. A layer 70 is on top of the central region 30. A layer 235 is on top of the side regions 260. A layer 230 is on top of the substrate 110. A layer 120 is on top of the central region 30. A layer 150 is on top of the side regions 260. A layer 264 is on top of the side regions 260. A layer 280 is on top of the central region 30. A layer 320 is on top of the side regions 260.

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